CLAIMS

1. A method of forming an oxidation coat of an aluminum-containing member of a device for manufacturing a semiconductor or a display, the method comprising:

a) mixing a sulfuric acid, an oxalic acid, and a tartaric acid to manufacture an electrolytic solution; and

b) forming an anodic oxidation coat on a surface of an aluminum or aluminum alloy member using the electrolytic solution manufactured in step a),

wherein a content weight ratio of the sulfuric acid, the oxalic acid, and the tartaric acid in the step a) is 9 to 11 : 2.5 to 3.5 : 0.3 to 0.7, and

wherein the anodic oxidation coat has a thickness of 50 to 60 μm.

2. The method of claim 1, wherein a concentration of the electrolytic solution is 1 to 10 wt%.

3. The method of claim 1, wherein in the forming the anodic oxidation coat of step b), an applied current is 0.8 to 1.7 A/dm^2 and a temperature of the electrolytic solution is 8 to 22°C.

4. An aluminum-containing member having an anodic

oxidation coat of a device for manufacturing a semiconductor or a display, the anodic oxidation coat having a hardness of 370 to 425 Hv, a withstanding voltage of 1500 to 2000 V and a corrosion resistance of 120 minutes or more, and being formed on a surface thereof using the method of any one of claims 1 to 3.

5. An aluminum-containing member of a device for manufacturing a semiconductor or a display, the aluminum-containing member being coated with an anodic oxidation coat having a hardness of 370 to 425 Hv, a withstanding voltage of 1500 to 2000 V, a corrosion resistance of 120 minutes or more and a thickness of 50 to 60 μm.